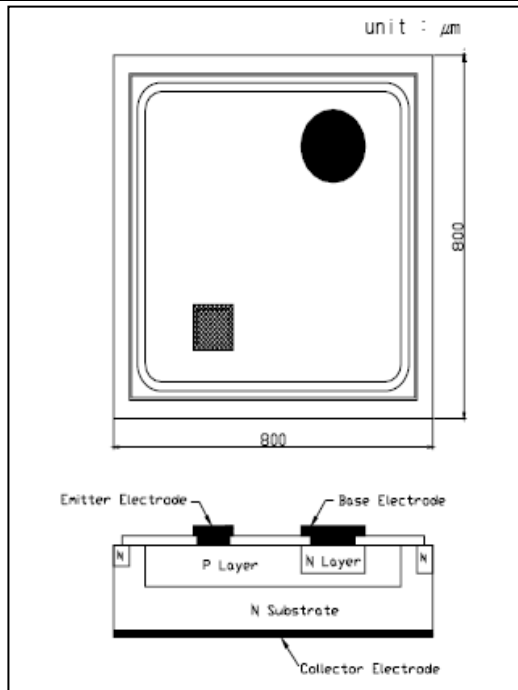


OPB0808

Silicon Photo Transistor

1. Structure

- 1.1 Chip Size : 0.80mm X 0.80mm
- 1.2 Chip thickness : 280±20um
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Emitter : 140um
 - Base : 100um X 100um
- 1.6 Active Area : 0.64mm X 0.64mm



2. Guaranteed Probed Electrical Characteristics

(Ta=25°C)

| Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|-------------------------|-------------|-----|-----|------|------|-----------------------|
| C-E Leakage Current | I_{CEO} | | | 100 | nA | $V_{CE}=10V$ |
| Spectrum Sensitivity | λ | 450 | | 1100 | nm | |
| Peak Sensing Wavelength | λ_p | | 880 | | nm | |
| C-E Voltage | BV_{CEO} | 40 | | | V | $I_{CE}=500\mu A$ |
| C-B Voltage | BV_{CBO} | 50 | | | V | $I_{CB}=50\mu A$ |
| E-B Voltage | BV_{EBO} | 6 | | | V | $I_{EB}=50\mu A$ |
| E-C Voltage | BV_{ECO} | 5 | | | V | $I_{EC}=50\mu A$ |
| C-E Saturation Voltage | V_{CES} | | | 300 | mV | $I_C=5mA, I_B=1mA$ |
| DC Current Gain | h_{FE} | 200 | | 1500 | - | $V_{CE}=10V, I_C=1mA$ |

3. Hfe Bin Grade

| Bin Grade | MIN | MAX |
|-----------|-----|-------|
| A | 200 | 500 |
| B | 500 | 900 |
| C | 900 | 1,500 |

4. Maximum Ratings

(Ta=25°C)

| Parameter | Symbol | Rating | Unit |
|---------------------------|-----------|--------|------|
| Collector-Emitter Voltage | V_{CEO} | 30 | V |
| Emitter-Collector Voltage | V_{ECO} | 5 | V |

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